

## Electronic Supplementary Information (ESI)

### Lone-pair stabilized channels in apatite-related structures

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Table S1. Crystal data and structure refinement for  $\text{Tb}_2\text{Pb}_3\text{Si}_3\text{O}_{12}$  at 293(2) K.

Empirical formula	$\text{Tb}_2\text{Pb}_3\text{Si}_3\text{O}_{12}$
Formula weight	1215.66
Temperature	293(2) K
Wavelength	0.71073 Å
Crystal system	hexagonal
Space group	$P6_3/m$
Unit cell dimensions	$a = 9.6395(2)$ Å $c = 6.8787(2)$ Å
Volume	553.54(3) Å <sup>3</sup>
Z	2
Density (calculated)	7.294 g/cm <sup>3</sup>
θ range for data collection	2.440 to 29.068°
Index ranges	-12≤h≤13, -12≤k≤12, -6≤l≤9
Reflections collected	5914
Independent reflections	522 [ $R_{\text{int}} = 0.0667$ ]
Completeness to $\theta = 25.242^\circ$	100%
Refinement method	Full-matrix least-squares on $F^2$
Data / restraints / parameters	522 / 0 / 37
Goodness-of-fit	1.136
Final R indices [I > 2σ(I)]	$R_{\text{obs}} = 0.0442$ , $wR_{\text{obs}} = 0.1208$
R indices [all data]	$R_{\text{all}} = 0.0460$ , $wR_{\text{all}} = 0.1221$

$R = \Sigma |F_o| - |F_c| / \Sigma |F_o|$ ,  $wR = \{\Sigma [w(|F_o|^2 - |F_c|^2)^2] / \Sigma [w(|F_o|^4)]\}^{1/2}$  and

$w = 1/[\sigma^2(F_o^2) + (0.0653P)^2 + 27.4284P]$  where  $P = (F_o^2 + 2F_c^2)/3$

Table S2. Atomic coordinates and equivalent isotropic displacement parameters for  $\text{Tb}_2\text{Pb}_3\text{Si}_3\text{O}_{12}$  at 293(2) K with estimated standard deviations in parentheses.

Label	x	y	z	Occupancy	$U_{\text{eq}}^*$
Pb	-0.0057(1)	0.7538(7)	0.7500	1	0.021(1)
Tb	0.3333(4)	0.6667(12)	0.5038(4)	1	0.010(1)
Si	0.4139(6)	1.0302(6)	0.7500	1	0.010(1)
O(1)	0.3533(18)	0.8400(16)	0.7500	1	0.017(3)
O(2)	0.6080(15)	1.1385(15)	0.7500	1	0.019(3)
O(3)	0.3635(17)	1.0953(14)	0.9420(14)	1	0.035(3)

\* $U_{\text{eq}}$  is defined as one third of the trace of the orthogonalized  $U_{ij}$  tensor.

Table S3. Bond lengths [ $\text{\AA}$ ] for  $\text{Tb}_2\text{Pb}_3\text{Si}_3\text{O}_{12}$  at 293(2) K with estimated standard deviations in parentheses.

Label	Distances
Pb-O(1)	2.375(13)
Pb-O(2)x2	2.384(12)
Pb-O(2)'x2	2.562(14)
Tb-O(1)x3	2.319(9)
Tb-O(2)x3	2.415(7)
Tb-O(3)x3	2.698(14)
Si-O(1)	1.622(13)
Si-O(2)	1.624(5)
Si-O(3)	1.638(14)
Si-O(4)	1.638(12)

Table S4. Selected Bond angles [ $^\circ$ ] for  $\text{Tb}_2\text{Pb}_3\text{Si}_3\text{O}_{12}$  at 293(2) K

Label	Angles
O(1)-Pb-O(2)	84.6(3)
O(1)-Pb-O(2)'	69.5(4)
O(2)'-Pb-O(2)	62.0(7)
O(3)-Tb-O(3)	72.7(4)
O(3)-Tb-O(1)	93.5(3)
O(3)-Tb-O(1)	146.8(4)
O(3)-Tb-O(2)	142.0(5)
O(3)-Tb-O(2)'	80.6(4)
O(3)-Si-O(1)	111.8(7)

Table S5. Crystal data for  $\text{Pb}_5\text{SiP}_2\text{O}_{12}$  at 293(2) K.

Empirical formula	$\text{Pb}_5\text{SiP}_2\text{O}_{12}$
Formula weight	2636.07
Temperature	293(2) K
Wavelength	0.71073 Å
Crystal system	hexagonal
Space group	$P6_3/m$
Unit cell dimensions	$a = 9.7637(14)$ Å $c = 7.2791(15)$ Å
Volume	600.9(2) Å <sup>3</sup>
Z	2
Density (calculated)	7.284 g/cm <sup>3</sup>
θ range for data collection	2.409 to 27.430°
Index ranges	-12≤h≤10, -12≤k≤12, -9≤l≤9
Reflections collected	5643
Independent reflections	495 [ $R_{\text{int}} = 0.0991$ ]
Completeness to $\theta = 25.242^\circ$	100%
Refinement method	Full-matrix least-squares on $F^2$
Data / restraints / parameters	495 / 0 / 24
Goodness-of-fit	1.437
Final R indices [I > 2σ(I)]	$R_{\text{obs}} = 0.0571$ , $wR_{\text{obs}} = 0.1043$
R indices [all data]	$R_{\text{all}} = 0.0590$ , $wR_{\text{all}} = 0.1051$
Extinction coefficient	0.0054(5)

$R = \sum ||F_o| - |F_c|| / \sum |F_o|$ ,  $wR = \{\sum [w(|F_o|^2 - |F_c|^2)^2] / \sum [w(|F_o|^4)]\}^{1/2}$  and

$w=1/[\sigma^2(F_o^2)+57.6948P]$  where  $P=(F_o^2+2F_c^2)/3$

Table S6. Atomic coordinates and equivalent isotropic displacement parameters for  $\text{Pb}_5\text{SiP}_2\text{O}_{12}$  at 293(2) K with estimated standard deviations in parentheses.

Label	x	y	z	Occupancy	$U_{\text{eq}}^*$
Pb(1)	0.2503(12)	0.0002(2)	0.2500	1	0.014(1)
Pb(2)	0.3333.33	-0.3333.33	0.0042(4)	1	0.013(3)
Si(3)	0.6210(7)	0.0187(8)	0.2500	0.333	0.003(2)
P(3)	0.6210(7)	0.0187(8)	0.2500	0.6666	0.003(2)

O(1)	0.5060(12)	0.0930(12)	0.2500	1	0.012(4)
O(2)	0.7292(17)	0.0786(17)	0.4218(17)	1	0.012(3)
O(3)	0.5200(13)	-0.1660(14)	0.2500	1	0.010(6)

\* $U_{eq}$  is defined as one third of the trace of the orthogonalized  $U_{ij}$  tensor.

Table S7. Selected bond lengths [Å] for  $Pb_5SiP_2O_{12}$  at 293(2) K.

Label	Distances
Pb(1)-O(1)	2.19(2)
Pb(1)-O(2)'x2	2.631(11)
Pb(1)-O(2)x2	2.548(14)
Pb(1)-O(3)	2.75(2)
Pb(2)-O(2)x3	2.75(2)
Pb(2)-O(3)x3	2.492(8)
Si/P(3)-O(1)	1.61(4)
Si/P(3)-O(2)x2	1.550(13)
Si/P(3)-O(3)	1.56(2)

Table S8. Selected bond angles [°] for  $Pb_5SiP_2O_{12}$  at 293(2) K.

Label	Angles
O(1)-Pb(1)-O(1)'	139.0(6)
O(1)-Pb(1)-O(3)	150.8(7)
O(1)-Pb(1)-O(3)'	71.7(3)
O(1)-Pb(1)-O(2)	79.3(6)
O(2)-Pb(1)-O(3)	95.7(7)
O(1)-(P/Si)-O(1)'	108.1(11)
O(1)-(P/Si)-O(2)	108.8(8)
O(1)-(P/Si)-O(3)	110.7(7)

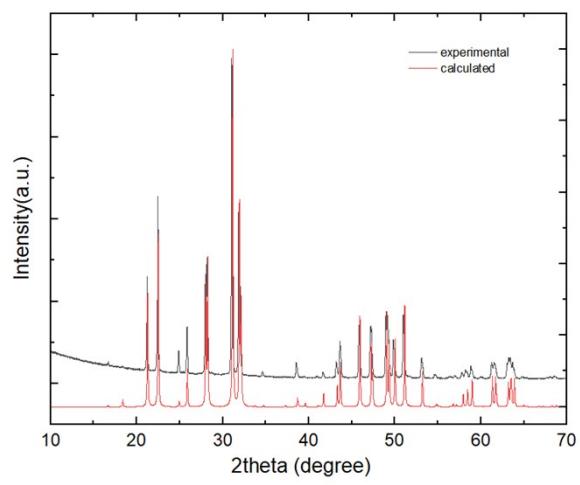


Figure S1. PXRD patterns for  $\text{Tb}_2\text{Pb}_3\text{Si}_3\text{O}_{12}$